#### Transistors

# 2SA2163

### Silicon PNP epitaxial planar type

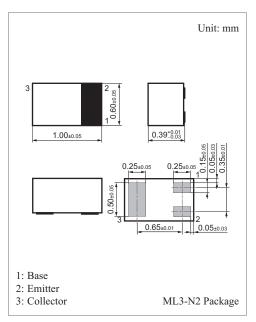
#### For high frequency amplification

#### Features

- High transition frequency f<sub>T</sub>
- Optimum for high-density mounting and downsizing of the equipment for Ultraminiature leadless package
  - $0.6~mm \times 1.0~mm$  (height 0.39 mm)

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-30	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-20	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-5	V	
Collector current	I <sub>C</sub>	-30	mA	
Collector power dissipation	P <sub>C</sub>	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	



#### Marking Symbol: 6J

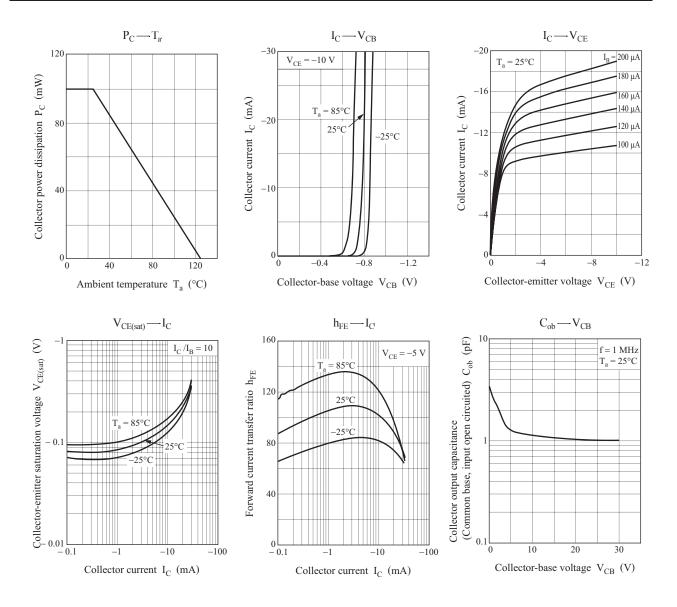
#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$		-0.7		V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -10 \text{ V}, I_{E'} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -20 \text{ V}, I_{B} = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{\rm EB} = -5 \text{ V}, I_{\rm C} = 0$			-10	μΑ
Forward current transfer ratio	$\mathbf{h}_{\mathrm{FE}}$	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$	70		220	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$		-0.1		V
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_{E} = 1 \text{ mA}, \text{ f} = 200 \text{ MHz}$	150	300		MHz
Noise figure	NF	$V_{CB} = -10 \text{ V}, I_{E} = 1 \text{ mA}, f = 5 \text{ MHz}$		2.8	4.0	dB
Reverse transfer impedance	Z <sub>rb</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 2 \text{ MHz}$		22	50	Ω
Reverse transfer capacitance (Common emitter)	C <sub>re</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 10.7 \text{ MHz}$		1.2	2.0	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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### **Panasonic**



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